

L Magafas

List of Publications by Year in descending order

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19
papers

146
citations

1307594

7
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1199594

12
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19
all docs

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docs citations

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times ranked

111
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Chaotic Behavior of the Forward I-V Characteristic of the Al/a-SiC:H/c-Si(n) Heterojunction. , 2013, , 475-479. | | 1 |
| 2 | DemoscopoPhysics. Advances in Business Strategy and Competitive Advantage Book Series, 2013, , 315-327. | 0.3 | 2 |
| 3 | Application of Physics Model in prediction of the Hellas National election results. Journal of Engineering Science and Technology Review, 2009, 2, 112-117. | 0.4 | 1 |
| 4 | Application of Physics Model in prediction of the Hellas Euro election results. Journal of Engineering Science and Technology Review, 2009, 2, 104-111. | 0.4 | 4 |
| 5 | Study of optical sensors of the form A l/a-SiC:H/c-Si(n) with high sensitivity. Journal of Engineering Science and Technology Review, 2008, 1, 41-44. | 0.4 | 5 |
| 6 | Electrical properties of annealed a-SiC:H thin films. Journal of Non-Crystalline Solids, 2007, 353, 1065-1069. | 3.1 | 6 |
| 7 | Optimization of Al/a-SiC:H optical sensor device by means of thermal annealing. Microelectronics Journal, 2007, 38, 1196-1201. | 2.0 | 4 |
| 8 | Optimization of the electrical properties of Al/a-SiC:H Schottky diodes by means of thermal annealing of a-SiC:H thin films. Microelectronics Journal, 2006, 37, 1352-1357. | 2.0 | 8 |
| 9 | Optical Response Study of the Al/a-SiC:H Schottky Diode for Different Substrate Temperatures of the R.F. Sputtered a-SiC:H Thin Film. Active and Passive Electronic Components, 2003, 26, 63-70. | 0.3 | 8 |
| 10 | Optical response of the Al/a-SiC/c-Si(p)/Au heterojunction structure. Microelectronics Journal, 2002, 33, 761-764. | 2.0 | 3 |
| 11 | The effect of thermal annealing on the optical properties of a-SiC:H films. Journal of Non-Crystalline Solids, 1998, 238, 158-162. | 3.1 | 14 |
| 12 | The a-SiC/c-Si(n) Isotype Heterojunction as a High Sensitivity Temperature Sensor. Active and Passive Electronic Components, 1998, 20, 225-234. | 0.3 | 1 |
| 13 | The influence of metal work function on electrical properties of metal/ a-SiC:H Schottky diodes. Microelectronics Journal, 1997, 28, 107-114. | 2.0 | 11 |
| 14 | Optical properties of $\hat{I}\pm$ -SiC:H thin films grown by rf sputtering. Physical Review B, 1994, 49, 8191-8197. | 3.2 | 15 |
| 15 | A Study of a-SiC/C-Si(n) Isotype Heterojunctions. Active and Passive Electronic Components, 1993, 16, 55-64. | 0.3 | 3 |
| 16 | Electrical properties of a-SiC/c-Si(p) heterojunctions. Semiconductor Science and Technology, 1992, 7, 1363-1368. | 2.0 | 40 |
| 17 | Structural and optical properties of a-SiC:H thin films. Journal of Non-Crystalline Solids, 1992, 139, 146-150. | 3.1 | 7 |
| 18 | The Dependence of Electrical and Optical Properties of RF Sputtered Amorphous Siliconâ€“Carbon Alloy Thin Films on Substrate Temperature and Hydrogen Flow Rate. Physica Status Solidi A, 1991, 126, 143-150. | 1.7 | 12 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | The Influence of Deposition Conditions on the Properties of a-Si:H Thin Films. Materials Research Society Symposia Proceedings, 1990, 192, 589. | 0.1 | 1 |